

TRANSISTOR MODULE

QCA150AA100

TOP



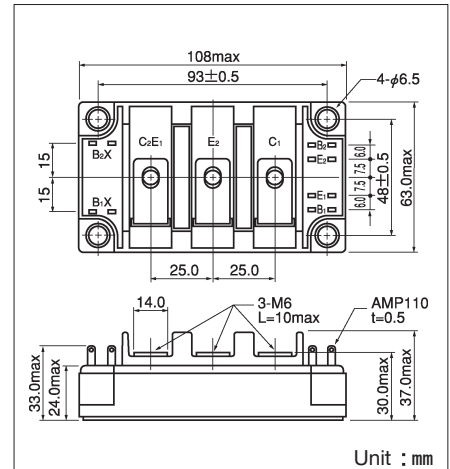
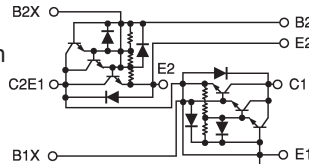
UL;E76102 (M)

QCA150AA100 is a dual Darlington power transistor module which has series-connected high speed, high power Darlington transistors. Each transistor has a reverse paralleled fast recovery diode. The mounting base of the module is electrically isolated from semiconductor elements for simple heatsink construction,

- $I_C=150A$, $V_{CEX}=1000V$
- Low saturation voltage for higher efficiency.
- High DC current gain h_{FE}
- Isolated mounting base

(Applications)

Motor Control (VVVF), AC/DC Servo, UPS,
Switching Power Supply, Ultrasonic Application



Unit : mm

Maximum Ratings

($T_j=25^\circ C$)

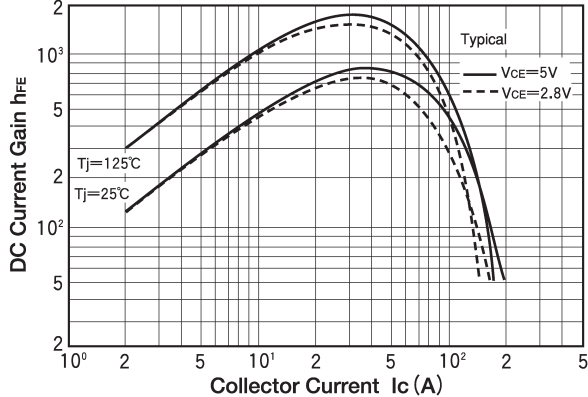
Symbol	Item		Conditions	Ratings	Unit
				QCA150AA100	
V_{CBO}	Collector-Base Voltage			1000	V
V_{CEX}	Collector-Emitter Voltage		$V_{BE} = -2V$	1000	V
V_{EBO}	Emitter-Base Voltage			7	V
I_C	Collector Current			150	A
$-I_C$	Reverse Collector Current			150	A
I_B	Base Current			8	A
P_T	Total power dissipation		$T_C=25^\circ C$	1000	W
T_j	Junction Temperature			$-40 \sim +150$	$^\circ C$
T_{stg}	Storage Temperature			$-40 \sim +125$	$^\circ C$
V_{ISO}	Isolation Voltage		A.C.1minute	2500	V
	Mounting Torque	Mounting (M6)	Recommended Value 2.5~3.9 (25~40)	4.7 (48)	N·m (kgf·cm)
		Terminal (M6)	Recommended Value 2.5~3.9 (25~40)	4.7 (48)	
	Mass		Typical Value	540	g

Electrical Characteristics

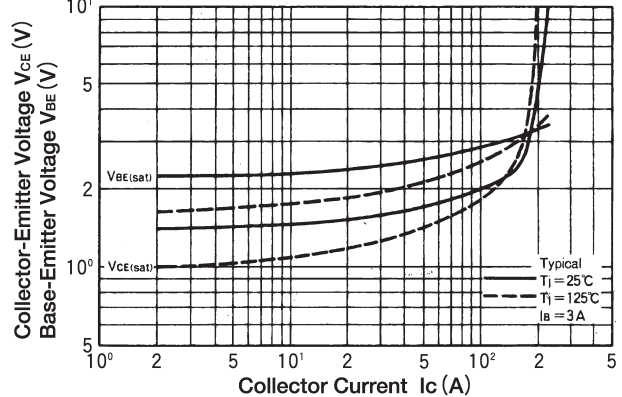
($T_j=25^\circ C$)

Symbol	Item		Conditions	Ratings		Unit
				Min.	Max.	
I_{CBO}	Collector Cut-off Current		$V_{CB}=1000V$		1.0	mA
I_{EBO}	Emitter Cut-off Current		$V_{EB}=7V$		400	mA
$V_{CEX(SUS)}$	Collector Emitter Sustaining Voltage		$I_C=30A$, $I_{B2}=-5A$	1000		V
h_{FE}	DC Current Gain		$I_C=150A$, $V_{CE}=2.8V$	75		
			$I_C=150A$, $V_{CE}=5V$	100		
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage		$I_C=150A$, $I_B=3A$		2.5	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage		$I_C=150A$, $I_B=3A$		3.5	V
t_{on}	Switching Time	On Time	$V_{CC}=600V$, $I_C=150A$ $I_{B1}=3A$, $I_{B2}=-3A$		3.0	μs
t_s		Storage Time			15.0	
t_f		Fall Time			3.0	
V_{ECO}	Collector-Emitter Reverse Voltage		$-I_C=150A$		1.8	V
$R_{th(j-c)}$	Thermal Impedance (junction to case)		Transistor part		0.125	$^\circ C/W$
			Diode part		0.6	

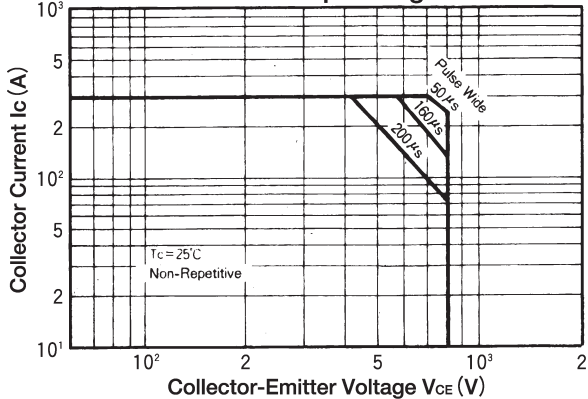
D.C. Current Gain



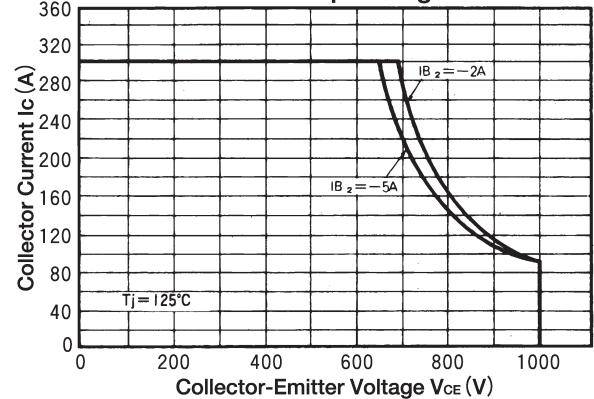
Saturation Characteristics



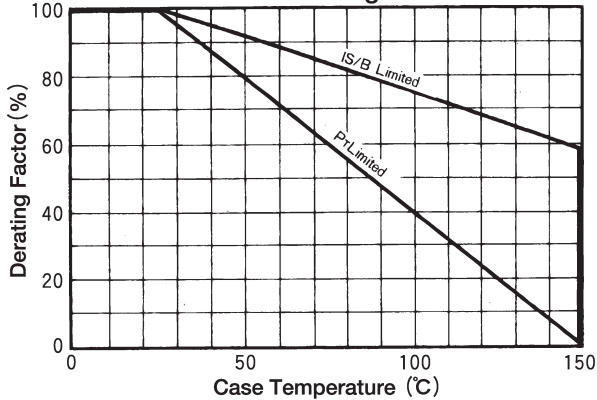
Forward Bias Safe Operating Area



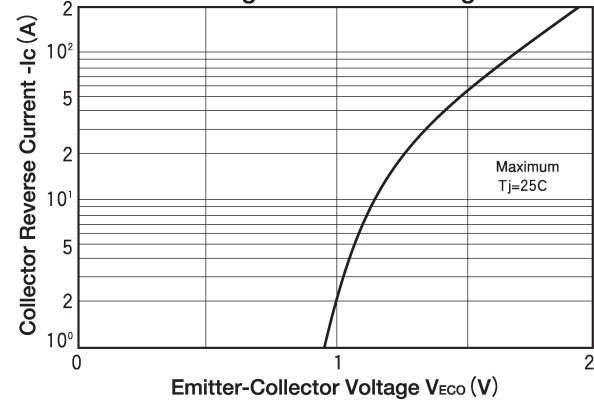
Reverse Bias Safe Operating Area



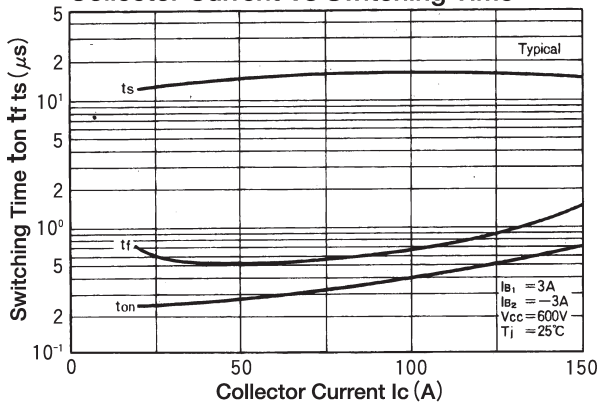
Collector Current Derating Factor



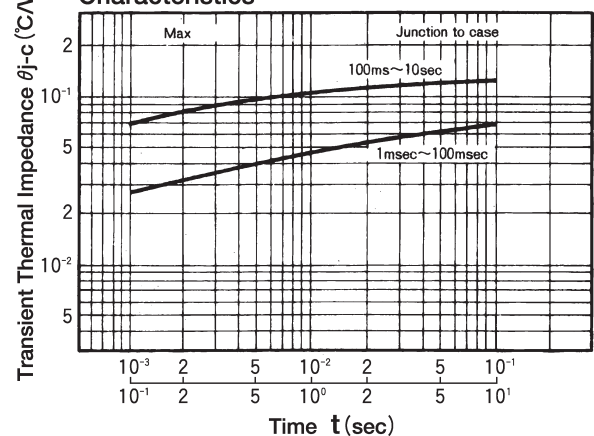
Forward Voltage of Free Wheeling Diode



Collector Current Vs Switching Time



Maximum Transient Thermal Impedance Characteristics



TRANSISTOR MODULE

QCA150AA120

TOP



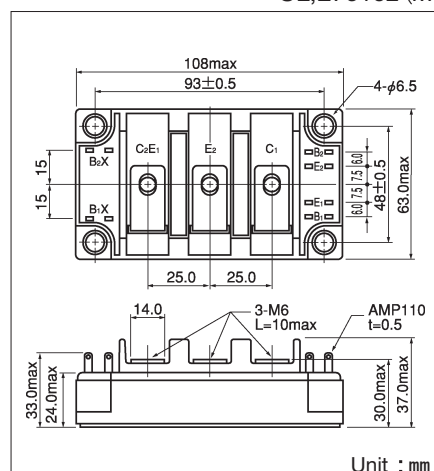
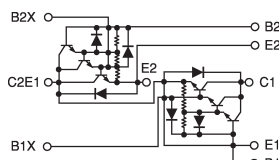
UL;E76102 (M)

QCA150AA120 is a dual Darlington power transistor module which has series-connected high speed, high power Darlington transistors. Each transistor has a reverse paralleled fast recovery diode. The mounting base of the module is electrically isolated from semiconductor elements for simple heatsink construction,

- $I_C=150A$, $V_{CEX}=1200V$
- Low saturation voltage for higher efficiency.
- High DC current gain h_{FE}
- Isolated mounting base

(Applications)

Motor Control (VVVF), AC/DC Servo, UPS,
Switching Power Supply, Ultrasonic Application



Maximum Ratings

($T_j=25^\circ C$)

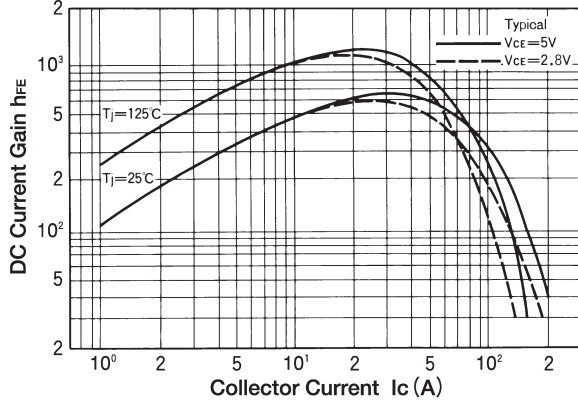
Symbol	Item		Conditions	Ratings	Unit
				QCA150AA120	
V_{CBO}	Collector-Base Voltage			1200	V
V_{CEX}	Collector-Emitter Voltage		$V_{BE} = -2V$	1200	V
V_{EBO}	Emitter-Base Voltage			10	V
I_C	Collector Current			150	A
$-I_C$	Reverse Collector Current			150	A
I_B	Base Current			8	A
P_T	Total power dissipation		$T_C=25^\circ C$	1000	W
T_j	Junction Temperature			$-40 \sim +150$	$^\circ C$
T_{stg}	Storage Temperature			$-40 \sim +125$	$^\circ C$
V_{ISO}	Isolation Voltage		A.C.1minute	2500	V
	Mounting Torque	Mounting (M6)	Recommended Value 2.5~3.9 (25~40)	4.7 (48)	N·m (kgf·cm)
		Terminal (M6)	Recommended Value 2.5~3.9 (25~40)	4.7 (48)	
	Mass		Typical Value	470	g

Electrical Characteristics

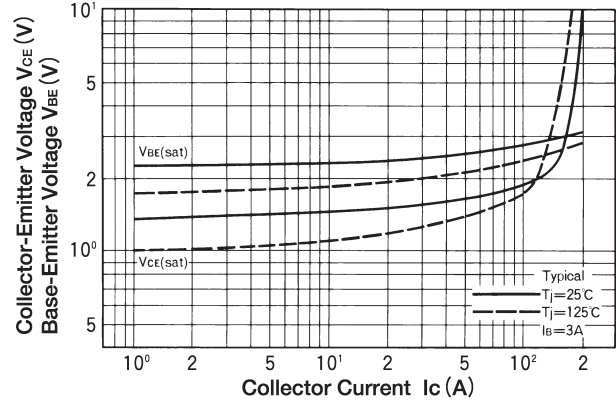
($T_j=25^\circ C$)

Symbol	Item		Conditions	Ratings		Unit
				Min.	Max.	
I_{CBO}	Collector Cut-off Current		$V_{CB}=1200V$		2.0	mA
I_{EBO}	Emitter Cut-off Current		$V_{EB}=10V$		600	mA
$V_{CEX(SUS)}$	Collector Emitter Sustaining Voltage		$I_C=30A$, $I_{B2}=-6A$	1200		V
h_{FE}	DC Current Gain		$I_C=150A$, $V_{CE}=5V$	75		
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage		$I_C=150A$, $I_B=3A$		3.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage		$I_C=150A$, $I_B=3A$		3.5	V
t_{on}	Switching Time	On Time	$V_{CC}=600V$, $I_C=150A$ $I_{B1}=3A$, $I_{B2}=-3A$		3.0	μs
t_s		Storage Time			15.0	
t_f		Fall Time			3.0	
V_{ECO}	Collector-Emitter Reverse Voltage		$-I_C=150A$		1.8	V
$R_{th(j-c)}$	Thermal Impedance (junction to case)		Transistor part		0.125	$^\circ C/W$
			Diode part		0.6	

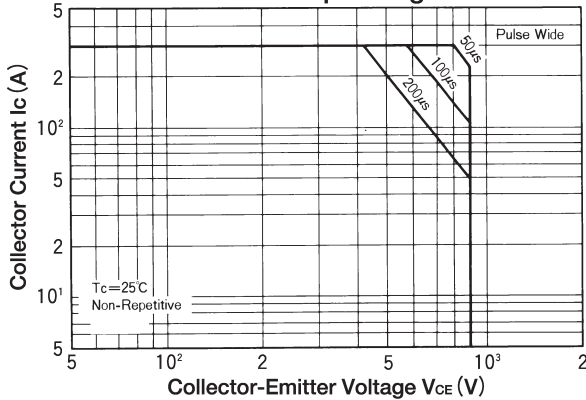
D.C. Current Gain



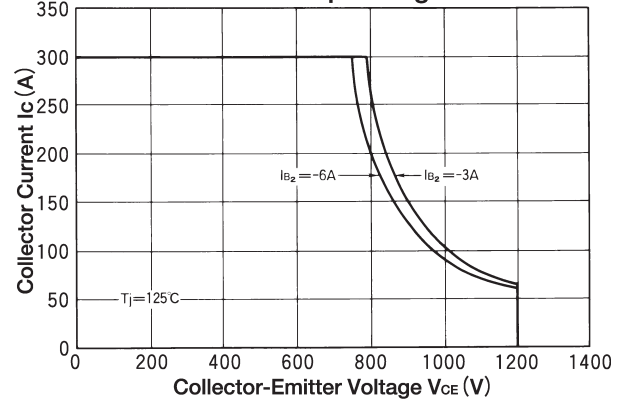
Saturation Characteristics



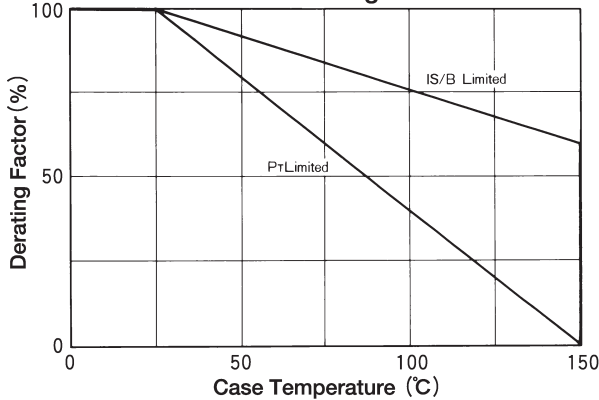
Forward Bias Safe Operating Area



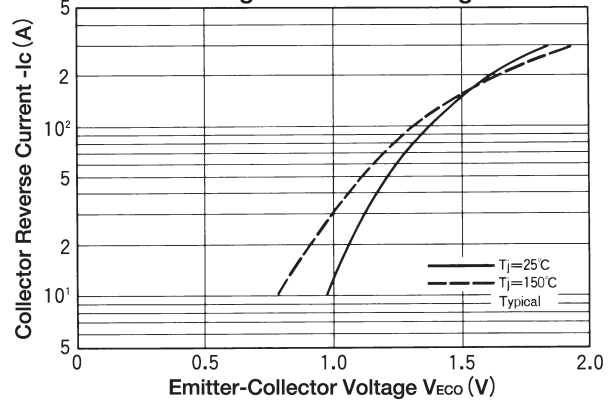
Reverse Bias Safe Operating Area



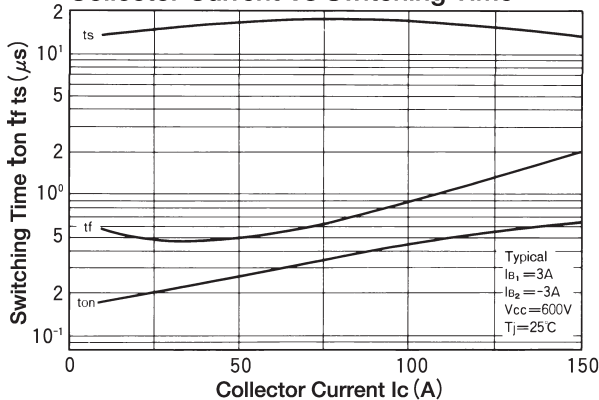
Collector Current Derating Factor



Forward Voltage of Free Wheeling Diode



Collector Current Vs Switching Time



Maximum Transient Thermal Impedance Characteristics

